

LMG342xR030 600-V 30-mΩ GaN FET with Integrated Driver, Protection, and Temperature Reporting

1 Features

- Qualified for JEDEC JEP180 for hard-switching topologies
- 600-V GaN-on-Si FET with Integrated gate driver
 - Integrated high precision gate bias voltage
 - 200-V/ns CMTI
 - 2.2-MHz switching frequency
 - 30-V/ns to 150-V/ns slew rate for optimization of switching performance and EMI mitigation
 - Operates from +12-V unregulated supply
- Robust protection
 - Cycle-by-cycle overcurrent and latched short-circuit protection with < 100-ns response
 - Withstands 720-V surge while hard-switching
 - Self-protection from internal overtemperature and UVLO monitoring
- Advanced power management
 - Digital temperature PWM output
 - Ideal diode mode reduces third-quadrant losses in LMG3425R030

2 Applications

- High density industrial power supplies
- Solar inverters and industrial motor drives
- Uninterruptable power supplies

3 Description

The LMG342xR030 GaN FET with integrated driver and protection enables designers to achieve new levels of power density and efficiency in power electronics systems.

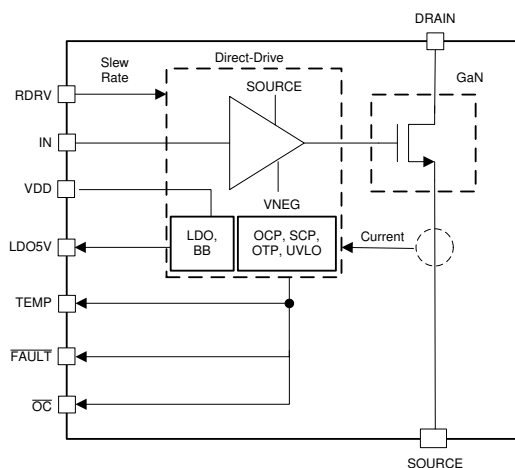
The LMG342xR030 integrates a silicon driver that enables switching speed up to 150 V/ns. TI's integrated precision gate bias results in higher switching SOA compared to discrete silicon gate drivers. This integration, combined with our low-inductance package, delivers clean switching and minimal ringing in hard-switching power supply topologies. Other features, including adjustable gate drive strength for EMI control, overtemperature, and robust overcurrent protection with fault indication, provide optimized BOM cost, board size, and footprint.

Advanced power management features include digital temperature reporting and TI's ideal diode mode. The temperature of the GaN FET is reported through a variable duty cycle PWM output, which enables the system to optimally manage loading. Ideal diode mode maximizes efficiency by reducing third-quadrant losses by enabling adaptive dead-time control.

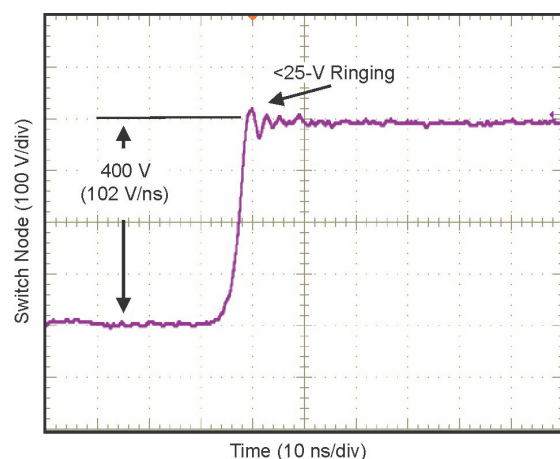
Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
LMG342xR030	VQFN (54)	12.00 mm × 12.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Simplified Block Diagram



Switching Performance at > 100 V/ns



6 Pin Configuration and Functions

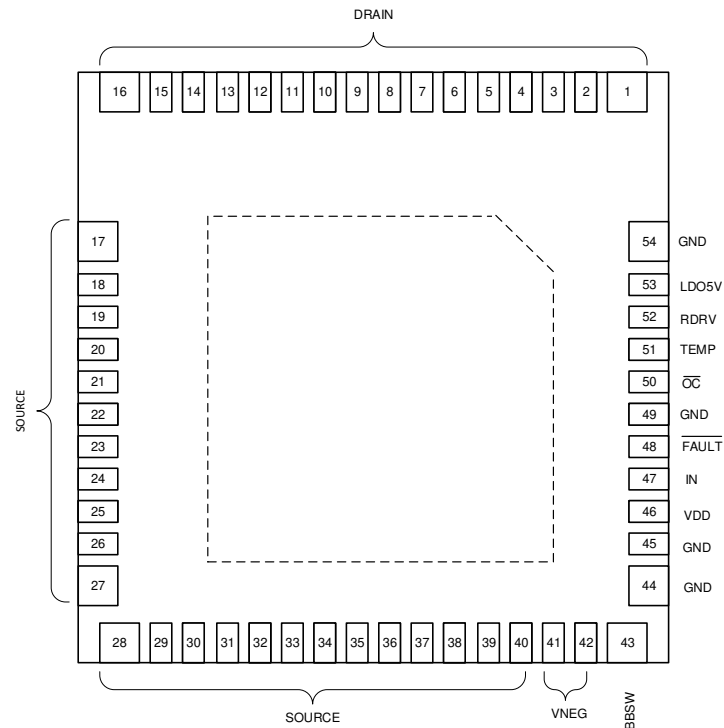


Figure 6-1. RQZ (VQFN) Package 54 Pins (Top View)

Table 6-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.		
BBSW	43	P	Internal buck-boost converter switch pin. Connect an inductor from this point to ground.
DRAIN	1-16	P	Power transistor drain.
FAULT	48	O	Fault output, push-pull, active low. Refer to Section 9.3.6 for details.
IN	47	I	CMOS-compatible noninverting gate drive input.
LDO5V	53	P	5-V LDO output for external digital isolator.
OC	50	O	Overcurrent and short-circuit fault output, push-pull, active low. Refer to Section 9.3.6 for details.
SOURCE	17-40	P	Power transistor source, die-attach pad, thermal sink, power ground reference.
RDRV	52	I	Drive strength selection pin. Connect a resistor from this pin to ground to set the turn-on drive strength to control slew rate. Tie the pin to GND to enable 150 V/ns and tie the pin to LDO5V to enable 100 V/ns.
VDD	46	P	12-V power input, relative to source. Supplies 5-V rail and gate drive supply.
VNEG	41, 42	P	Negative supply output, bypass to ground with 2.2-μF capacitor.
TEMP	51	O	Temperature-sensing output.
PAD	—	P	Thermal pad at bottom tied to device source.
GND	44, 45, 49, 54	P	Signal ground reference.

(1) I = input, O = output, P = power, NU = make no external connection

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (October 2020) to Revision B (April 2021)	Page
• Added Device Comparison Table.....	5
• Updated Specifications tables.....	6
• Added Drain-Source Voltage Capability topic.....	15

Changes from Revision * (September 2020) to Revision A (October 2020)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Changed the data sheet status from Product Preview to Advanced Information.....	1

5 Device Comparison

Table 5-1. Device Comparison Table

DEVICE NAME	DUAL OVERCURRENT / SHORT-CIRCUIT PROTECTION	TEMPERATURE REPORTING	IDEAL DIODE MODE
LMG3422R030	Yes	Yes	No
LMG3425R030	Yes	Yes	Yes

7 Specifications

7.1 Absolute Maximum Ratings

Unless otherwise noted: voltages are respect to GND, SOURCE connected to GND⁽¹⁾

		MIN	MAX	UNIT
V_{DS}	Drain-source voltage (FET Off)		600	V
$V_{DS(surge)}$	Drain-source surge voltage (FET Switching) ⁽²⁾		720	V
$V_{DS(tr)}$	Drain-source transient ringing peak voltage (FET Off) ^{(2) (3)}		800	V
Pin voltage	VDD	−0.3	20	V
	LDO5V	−0.3	5.5	V
	VNEG	−16	0.3	V
	BBSW	$V_{VNEG}-1$	$V_{VDD}+0.5$	V
	IN	−0.3	20	V
	FAULT, $\overline{OC}$, TEMP	−0.3	$V_{LDO5V}+0.3$	V
	RDRV	−0.3	5.5	V
$I_{D(RMS)}$	Drain RMS current (FET On)		55	A
$I_{D(pulse)}$	Drain pulsed current (FET On, $t_p < 10 \mu s$) ⁽⁴⁾	−120	Internally Limited	A
$I_{S(pulse)}$	Source pulsed current (FET Off, $t_p < 1 \mu s$)		80	A
T_J	Operating junction temperature ⁽⁵⁾	−40	150	°C
T_{stg}	Storage temperature	−55	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) See [Section 9.3.2](#) for an explanation of the switching cycle drain-source voltage ratings.
- (3) $t_1 < 200$ ns in [Figure 9-2](#).
- (4) The positive pulsed current must remain below the overcurrent threshold to avoid the FET being automatically shut off. The FET drain intrinsic positive pulsed current rating for $t_p < 10 \mu s$ is 120 A.
- (5) Refer to the Electrical and Switching Characteristics Tables for junction temperature test conditions.

7.2 ESD Ratings

	PARAMETER	VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins ⁽¹⁾	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

Unless otherwise noted: voltages are respect to GND, SOURCE connected to GND

		MIN	NOM	MAX	UNIT
	Supply voltage	7.5	12	18	V
	Input voltage	0	5	18	V
$I_{D(RMS)}$	Drain RMS current			40	A
	Positive source current			25	mA
R_{RDRV}	RDRV to GND resistance from external slew-rate control resistor	0		500	k Ω
C_{VNEG}	VNEG to GND capacitance from external bypass capacitor	1		10	μF

Unless otherwise noted: voltages are respect to GND, SOURCE connected to GND

		MIN	NOM	MAX	UNIT
L _{BBSW}	BBSW to GND inductance from external buck-boost inductor	3	4.7	10	uH

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		LMG342xR030	UNIT
		RQZ (VQFN)	
		54 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	16.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	4.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	3.1	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	0.12	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	0.33	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

Unless otherwise noted: voltage, resistance, capacitance, and inductance are respect to GND; $-40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C}$; $V_{DS} = 480\text{ V}$; $9\text{ V} \leq V_{VDD} \leq 18\text{ V}$; $V_{IN} = 5\text{ V}$; SOURCE connected to GND; RDRV connected to LDO5V; $L_{BBSW} = 4.7\text{ }\mu\text{H}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
GAN POWER TRANSISTOR						
R _{DS(on)}	Drain-source on resistance	T _J = 25 °C		30		mΩ
		T _J = 125 °C		56		mΩ
V _{SD}	Third-quadrant mode source-drain voltage	V _{IN} = 0 V, I _S = 0.1 A		5		V
		V _{IN} = 0 V, I _S = 20 A		7		V
I _{DSS}	Drain leakage current	V _{IN} = 0 V, V _{DS} = 600 V, T _J = 25 °C		1		uA
		V _{IN} = 0 V, V _{DS} = 600 V, T _J = 125 °C		10		uA
C _{OSS}	Output capacitance	V _{IN} = 0 V, V _{DS} = 400 V		218		pF
C _{O(er)}	Energy related effective output capacitance	V _{IN} = 0 V, V _{DS} = 0 V to 400 V		276		pF
C _{O(tr)}	Time related effective output capacitance			438		pF
Q _{OSS}	Output charge			175		nC
Q _{RR}	Reverse recovery charge			0		nC
VDD – SUPPLY CURRENTS						
	VDD quiescent current (LMG3422)	V _{VDD} = 12 V, V _{IN} = 0 V or 5V		700	1200	uA
	VDD quiescent current (LMG3425)	V _{VDD} = 12 V, V _{IN} = 0 V or 5V		780	1300	uA
	VDD operating current	V _{VDD} = 12 V, f _{IN} = 140 kHz, soft-switching		16	19	mA
BUCK BOOST CONVERTER						
	VNEG output voltage	VNEG sinking 50 mA		–14		V
	BBSW switching frequency	V _{VDD} = 9 V, VNEG sinking 150 mA, Peak sourcing BBSW = 1 A (Peak external buck-boost inductor current)		700		kHz
	Peak BBSW sourcing current at low peak current mode setting (Peak external buck-boost inductor current)	VNEG sinking 25 mA	0.3	0.4	0.5	A

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 $V_{DS} = 480\text{ V}$; $9\text{ V} \leq V_{VDD} \leq 18\text{ V}$; $V_{IN} = 5\text{ V}$; SOURCE connected to GND; RDRV connected to LDO5V; $L_{BBSW} = 4.7\text{ }\mu\text{H}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Peak BBSW sourcing current at high peak current mode setting (Peak external buck-boost inductor current)	VNEG sinking 100 mA	0.8	1	1.2	A
	High peak current mode setting enable – BBSW positive-going input threshold frequency		280	400	515	kHz
LDO5V						
	Output voltage	LDO5V sourcing 25 mA	4.75	5	5.25	V
	Short-circuit current		25	50	100	mA
IN						
$V_{IN,IT+}$	Positive-going input threshold voltage		1.7		2.45	V
$V_{IN,IT-}$	Negative-going input threshold voltage		0.7		1.3	V
	Input threshold hysteresis		0.8	1	1.5	V
	Input pulldown resistance	$V_{IN} = 2\text{ V}$	100	150	200	k Ω
FAULT, OC, TEMP – OUPUT DRIVE						
	Low-level output voltage	Output sinking 8 mA		0.16	0.4	V
	High-level output voltage	Output sourcing 8 mA, Measured as $V_{LDO5V} - V_O$		0.2	0.4	V
VDD, VNEG – UNDER VOLTAGE LOCKOUT						
$V_{VDD,T(UVLO)+}$	VDD UVLO – positive-going threshold voltage		6.6	7	7.5	V
	VDD UVLO – negative-going threshold voltage		6.1	6.5	6.8	V
	VDD UVLO – Input threshold voltage hysteresis			680		mV
	VNEG UVLO – negative-going threshold voltage		-13.6	-13.0	-12.4	V
	VNEG UVLO – positive-going threshold voltage		-13.2	-12.75	-12.2	V
GATE DRIVER						
	Turn-on drain slew rate	From $V_{DS} < 320\text{ V}$ to $V_{DS} < 80\text{ V}$, RDRV disconnected from LDO5V, $R_{RDRV} = 200\text{ k}\Omega$, $T_J = 25\text{ }^{\circ}\text{C}$, $V_{BUS} = 400\text{ V}$, I_{HB} current = 10 A, see Figure 8-1		20		V/ns
		From $V_{DS} < 320\text{ V}$ to $V_{DS} < 80\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$, $V_{BUS} = 400\text{ V}$, I_{HB} current = 10 A, see Figure 8-1		100		V/ns
		From $V_{DS} < 320\text{ V}$ to $V_{DS} < 80\text{ V}$, RDRV disconnected from LDO5V, $V_{RDRV} = 0\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$, $V_{BUS} = 400\text{ V}$, I_{HB} current = 10 A, see Figure 8-1		150		V/ns
	Slew rate variation	From $V_{DS} < 320\text{ V}$ to $V_{DS} < 80\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$, $V_{BUS} = 400\text{ V}$, I_{HB} current = 10 A, see Figure 8-1		25		%
$f_{IN(max)}$	Maximum GaN FET switching frequency.	V_{NEG} rising to $> -13.25\text{ V}$, soft-switched, maximum switching frequency derated for $V_{VDD} < 9\text{ V}$	2.2			MHz
FAULTS						
$I_{T(OC)}$	DRAIN overcurrent fault – threshold current		60	70	80	A

Unless otherwise noted: voltage, resistance, capacitance, and inductance are respect to GND; $-40\text{ }^{\circ}\text{C} \leq T_J \leq 125\text{ }^{\circ}\text{C}$;
 $V_{DS} = 480\text{ V}$; $9\text{ V} \leq V_{VDD} \leq 18\text{ V}$; $V_{IN} = 5\text{ V}$; SOURCE connected to GND; RDRV connected to LDO5V; $L_{BBSW} = 4.7\text{ }\mu\text{H}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{T(SC)}	DRAIN short-circuit fault – threshold current		80	95	110	A
	di/dt threshold between overcurrent and short-circuit faults		150			A/μs
	Short-circuit current to overcurrent fault trip difference			25		A
	GaN temperature fault – postive-going threshold temperature			175		°C
	GaN Temperature fault – threshold temperature hysteresis			30		°C
	Driver temperature fault – positive-going threshold temperature			185		°C
	Driver Temperature fault – threshold temperature hysteresis			20		°C
TEMP						
	Output Frequency		6	11	18	kHz
	Output PWM Duty Cycle	GaN T _J = 150 °C		80		%
		GaN T _J = 125 °C		64.6		%
		GaN T _J = 85 °C		40		%
		GaN T _J = 25 °C		3		%
THIRD-QUADRANT CONTROL (LMG3425)						
V _{T(3rd)}	Drain-source third-quadrant detection – threshold voltage	V _{IN} = 0 V	–0.15	0	0.15	V
I _{T(ZC)}	Drain zero-current detection – threshold current	V _{IN} = 0 V	–0.2	0	0.2	A

7.6 Switching Characteristics

Unless otherwise noted: voltage, resistance, capacitance, and inductance are respect to GND; $-40\text{ }^{\circ}\text{C} \leq T_J \leq 125\text{ }^{\circ}\text{C}$;
 $V_{DS} = 480\text{ V}$; $9\text{ V} \leq V_{VDD} \leq 18\text{ V}$; $V_{IN} = 5\text{ V}$; SOURCE connected to GND; RDRV connected to LDO5V; $L_{BBSW} = 4.7\text{ }\mu\text{H}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SWITCHING TIMES						
$t_{pd(on)}$	Driver turn-on propagation delay	From $V_{IN} > V_{IN,IT+}$ to $I_D > 1\text{ A}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1 and Figure 8-2		30	55	ns
$t_{d(on)}$	Turn-on delay	From $I_D > 1\text{ A}$ to $V_{DS} < 320\text{ V}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1 and Figure 8-2		5	6	ns
$t_{r(on)}$	Turn-on rise time	From $V_{DS} < 320\text{ V}$ to $V_{DS} < 80\text{ V}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1 and Figure 8-2		2.5	3	ns
$t_{pd(off)}$	Driver turn-off propagation delay	From $V_{IN} < V_{IN,IT-}$ to $V_{DS} > 10\text{ V}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1 and Figure 8-2		32	50	ns
$t_{d(off)}$	Turn-off delay	From $V_{DS} > 10\text{ V}$ to $V_{DS} > 80\text{ V}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1 and Figure 8-2		8	10	ns
$t_{f(off)}$	Turn-off fall time ⁽¹⁾	From $V_{DS} > 80\text{ V}$ to $V_{DS} > 320\text{ V}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1 and Figure 8-2			23	ns
	Minimum IN high pulse-width for FET turn-on	V_{IN} rise/fall times $< 1\text{ ns}$, V_{DS} falls to $< 200\text{ V}$, $V_{BUS} = 400\text{ V}$, L_{HB} current = 10 A, see Figure 8-1			24	ns

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PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STARTUP TIMES						
	Driver start-up delay time	From $V_{VDD} > V_{VDD,T(UVLO)+}$ to $\overline{\text{FAULT}}$ high, $C_{LDO5V} = 100\text{ nF}$, $C_{VNEG} = 2.2\text{ }\mu\text{F}$ at 0-V bias linearly decreasing to $1.5\text{ }\mu\text{F}$ at 15-V bias			400	us
FAULT TIMES						
$t_{d(OC)}$	Overcurrent fault FET turn-off delay, FET on before overcurrent	From $I_D > I_{T(OC)}$ to FET off, $I_D\text{ di/dt} = 100\text{ A}/\mu\text{s}$		90	135	ns
$t_{d(OC)}$	Short-circuit current fault FET turn-off delay, FET on before short circuit	From $I_D > I_{T(SC)}$ to FET off, $I_D\text{ di/dt} = 700\text{ A}/\mu\text{s}$		90	135	ns
	Overcurrent fault FET turn-off delay, FET turning on into overcurrent	From FET turn-on to FET off		200	280	ns
	Short-circuit fault FET turn-off delay, FET turning on into short circuit	From FET turn-on to FET off		105	217	ns
$t_{d(\text{reset})}$	IN reset delay time to clear $\overline{\text{FAULT}}$ latch	From $V_{IN} < V_{IN,IT-}$ to $\overline{\text{FAULT}}$ high	250	350	580	us
THIRD QUADRANT CONTROL TIMES (LMG3425)						
$t_{d(idm_on)}$	Ideal diode mode FET turn-on delay time	$V_{DS} < V_{T(3rd)}$ to FET turn-on, $V_{DS}\text{ dv/dt} = -100\text{ V/ns}$ created with a half-bridge configuration inductor at 5 A		35	75	ns
$t_{d(idm_off)}$	Ideal diode mode FET turn-off delay time	$I_D > I_{T(ZC)}$ to FET turn-off, $I_D\text{ di/dt} = 100\text{ A}/\mu\text{s}$ created with a half-bridge configuration		30	68	ns

(1) During turn-off, V_{DS} rise time is the result of the resonance of C_{OSS} and loop inductance as well as load current.

8 Parameter Measurement Information

8.1 Switching Parameters

The circuit used to measure most switching parameters is shown in [Figure 8-1](#). The top LMG342xR030 device in this circuit is used to re-circulate the inductor current and functions in third-quadrant mode only. The bottom device is the active device that turns on to increase the inductor current to the desired test current. The bottom device is then turned off and on to create switching waveforms at a specific inductor current. Both the drain current (at the source) and the drain-source voltage is measured. The specific timing measurement is shown in [Figure 8-2](#). TI recommends to use the half-bridge as double pulse tester. Excessive third-quadrant operation may overheat the top device.

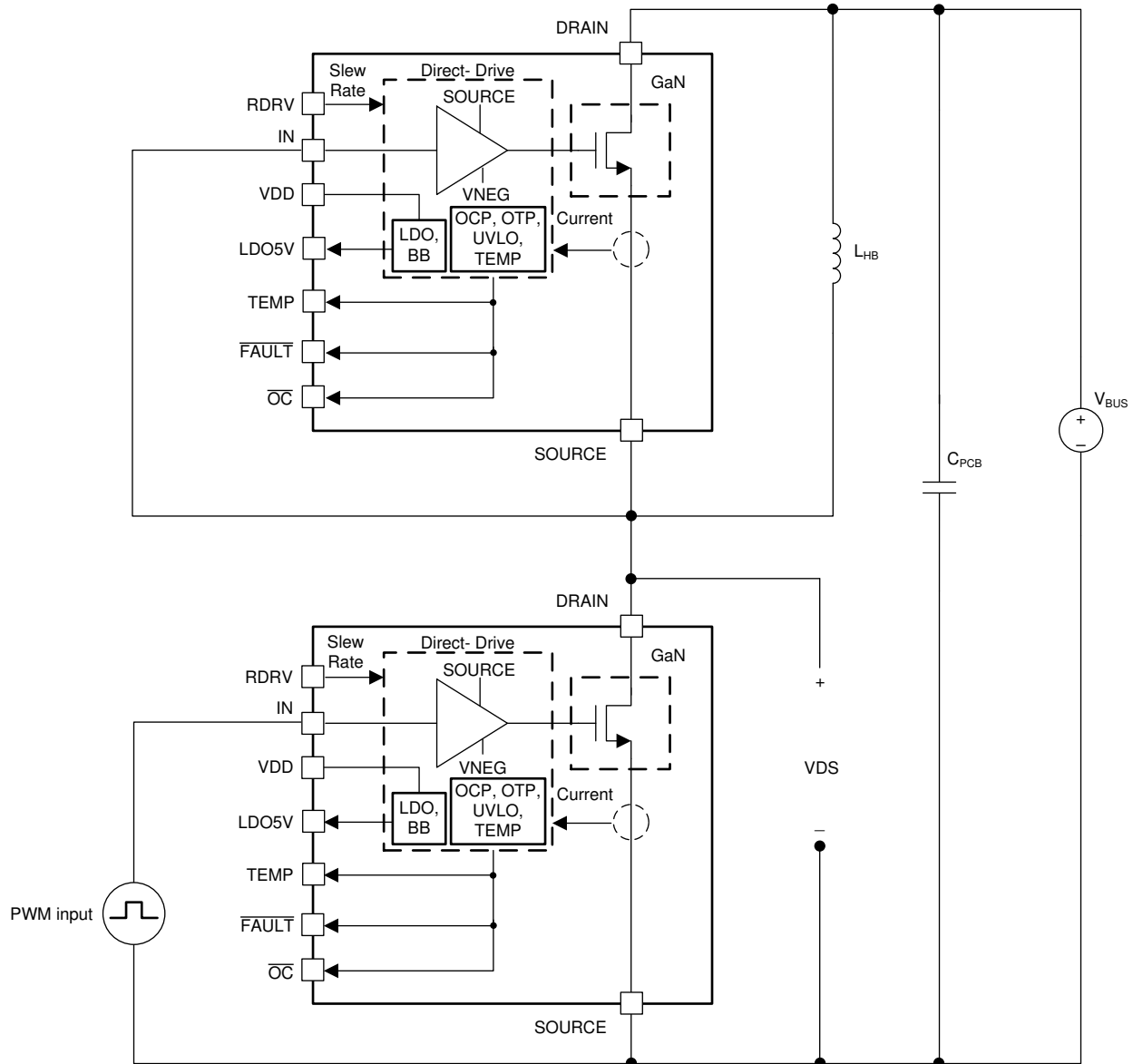


Figure 8-1. Circuit Used to Determine Switching Parameters

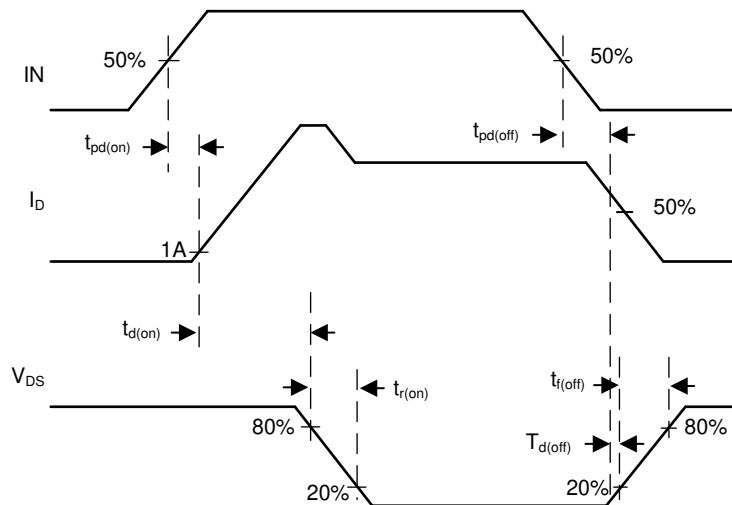


Figure 8-2. Measurement to Determine Propagation Delays and Slew Rates

8.1.1 Turn-On Delays

The timing of the turn-on transition has three components: propagation delay, turn-on delay, and fall time. The first component is the propagation delay of the driver from when the input goes high to when the GaN FET starts turning on (represented by 1-A drain current). The turn-on delay is the delay from when the FET starts turning on to when the drain voltage swings down by 20 percent. Finally, the V_{DS} fall time is the time it takes the drain voltage to slew between 80 percent and 20 percent of the bus voltage. The drive-strength resistor value has a large effect on turn-on delay and V_{DS} fall time, but does not affect the propagation delay significantly.

8.1.2 Turn-Off Delays

The timing of the turn-off transition has three components: propagation delay, turn-off delay, and rise time. The first component is the propagation delay of the driver from when the input goes low to when the GaN FET starts turning off. The turn-off delay is the delay from when the FET starts turning off (represented by the drain rising above 10 V) to when the drain voltage swings up by 20 percent. Finally, the V_{DS} rise time is the time it takes the drain voltage to slew between 20 percent and 80 percent of the bus voltage. The turn-off delays of the LMG342xR030 are independent of the drive-strength resistor, but the turn-off delay and the V_{DS} rise time are heavily dependent on the load current.

8.1.3 Drain Slew Rate

The slew rate, measured in volts per nanosecond, is measured on the turn-on edge of the LMG342xR030. The slew rate is considered over the V_{DS} fall time, which is when the drain falls from 80 percent to 20 percent of the bus voltage. The drain slew rate is thus given by 60 percent of the bus voltage divided by the V_{DS} fall time. This drain slew rate is dependent on the R_{DRV} value and is only slightly affected by the drain current.

9 Detailed Description

9.1 Overview

The LMG342xR030 is a high-performance power IC, GaN device with integrated gate driver. The GaN device offers zero reverse recovery and ultra-low output capacitance, which enables premium efficiency in bridge-based topologies. A Direct Drive architecture is applied to control the GaN device within the power IC. When the driver is powered up, the GaN device is controlled directly by the integrated gate driver. This architecture provides superior switching performance compared with the traditional cascode approach. The integrated driver solves a number of challenges in GaN applications.

The integrated driver ensures the device stays off for high drain slew rates. It also helps protect GaN device from overcurrent, short-circuit, undervoltage, and overtemperature. Regarding fault signal reporting, LMG342xR030 provides different reporting method which is shown in [Table 9-1](#). Refer to [Section 9.3.6](#) for more details. The integrated driver is also able to sense the die temperature and send out the temperature signal through a modulated PWM signal.

Unlike Si MOSFETs, there is no p-n junction from source to drain in GaN devices. That is why GaN devices have no reverse recovery charge. However, the GaN device can still conduct from source to drain in third-quadrant of operation similar to a body diode, but with higher voltage drop and higher conduction loss. Third-quadrant operation can be defined as follows: when the GaN device is turned off and negative current pulls the drain node voltage to be lower than its source, the voltage drop across the GaN device during third-quadrant operation is high. Therefore, TI recommends to operate with synchronous switching and keep the duration of third-quadrant operation at minimum.

9.2 Functional Block Diagram

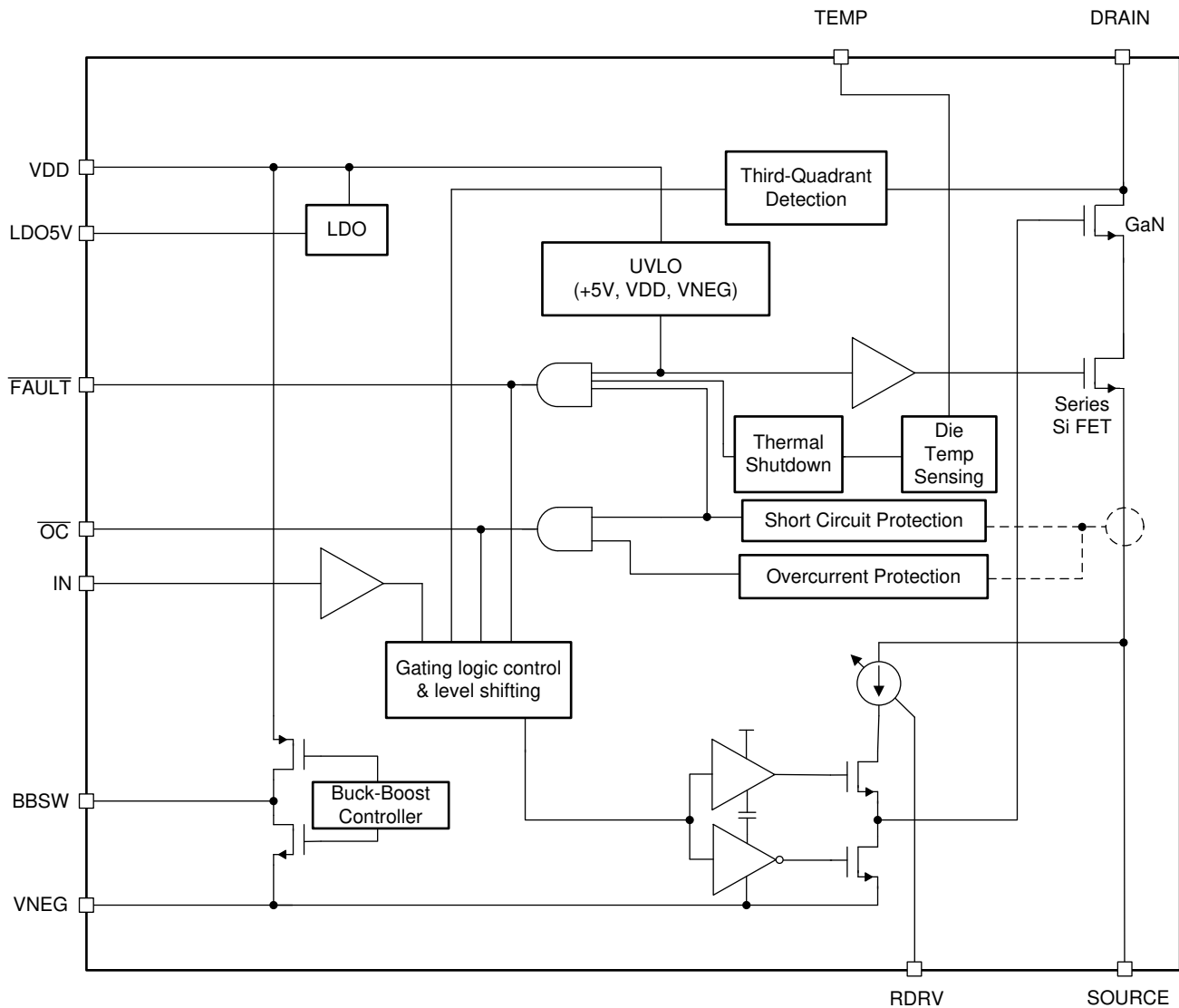


Figure 9-1. Simplified Block Diagram of LMG342xR030

9.3 Feature Description

The LMG342xR030 includes advanced features to provide premium switching performance and converter efficiency.

9.3.1 Direct-Drive GaN Architecture

The LMG342xR030 uses a series Si FET to ensure the power IC stays off when VDD bias power is not applied. When the VDD bias power is off, the series Si FET is interconnected with the GaN device in a cascode mode, which is shown in [Figure 9-1](#). The gate of the GaN device is held within a volt of the series Si FET's source. When a high voltage is applied on the module and the silicon FET blocks the drain voltage, the V_{GS} of the GaN device decreases until the GaN device passes the threshold voltage. Then, the GaN device is turned off and blocks the remaining major part of drain voltage. There is an internal clamp to make sure that the VDD does not exceed its maximum rating. This avoids the avalanche of the series Si FET when there is no bias power.

When LMG342xR030 is powered up with VDD bias power, the internal buck-boost converter generates a negative voltage (V_{NEG}) that is sufficient to directly turn off the GaN device. In this case, the series Si FET is held on and the GaN device is gated directly with the negative voltage. During operation, this removes the switching loss of the series Si FET.

9.3.2 Drain-Source Voltage Capability

Due to the silicon FET's long reign as the dominant power-switch technology, many designers are unaware that the headline drain-source voltage cannot be used as an equivalent point to compare devices across technologies. The headline drain-source voltage of a silicon FET is set by the avalanche breakdown voltage. The headline drain-source voltage of a GaN FET is set by the long term reliability with respect to datasheet specifications.

Exceeding the headline drain-source voltage of a silicon FET can lead to immediate and permanent damage. Meanwhile, the breakdown voltage of a GaN FET is much higher than the headline drain-source voltage. For example, the breakdown voltage of the LMG342xR030 is more than 800 V.

A silicon FET is usually the weakest link in a power application during an input voltage surge. Surge protection circuits must be carefully designed to ensure the silicon FET avalanche capability is not exceeded because it is not feasible to clamp the surge below the silicon FET breakdown voltage. Meanwhile, it is easy to clamp the surge voltage below a GaN FET breakdown voltage. In fact, a GaN FET can continue switching during the surge event which means output power is safe from interruption.

The LMG342xR030 drain-source capability is explained with the assistance of [Figure 9-2](#). The figure shows the drain-source voltage versus time for a GaN FET for a single switch cycle in a switching application. No claim is made about the switching frequency or duty cycle.

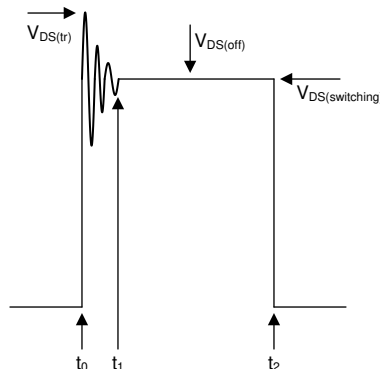


Figure 9-2. Drain-Source Voltage Switching Cycle

The waveform starts before t_0 with the FET in the on state. At t_0 the GaN FET turns off and parasitic elements cause the drain-source voltage to ring at high frequency. The peak ring voltage is designated $V_{DS(tr)}$. The high frequency ringing has damped out by t_1 . Between t_1 and t_2 the FET drain-source voltage is set by

the characteristic response of the switching application. The characteristic is shown as a flat line, but other responses are possible. The voltage between t_1 and t_2 is designated $V_{DS(off)}$. At t_2 the GaN FET is turned on at a non-zero drain-source voltage. The drain-source voltage at t_2 is designated $V_{DS(switching)}$. Unique $V_{DS(tr)}$, $V_{DS(off)}$ and $V_{DS(switching)}$ parameters are shown because each can contribute to stress over the lifetime of the GaN FET.

The LMG342xR030 drain-source surge voltage capability is seen with the absolute maximum ratings $V_{DS(tr)}$ and $V_{DS(surge)}$ in [Section 7.1](#) where $V_{DS(surge)}$ is the same as $V_{DS(off)}$ and $V_{DS(switching)}$ in [Figure 9-2](#). More information about the surge capability of TI GaN FETs is found in [A New Approach to Validate GaN FET Reliability to Power-line Surges Under Use-conditions](#).

9.3.3 Internal Buck-Boost DC-DC Converter

An internal inverting buck-boost converter generates a regulated negative rail for the turn-off supply of the GaN device. The buck-boost converter is controlled by a peak current mode, hysteretic controller. In normal operation, the converter remains in discontinuous-conduction mode, but may enter continuous-conduction mode during start-up and overload the conditions. The converter is controlled internally and requires only a single surface-mount inductor and output bypass capacitor.

The LMG342xR030 supports the GaN operation up to 2.2 MHz. As power consumption is very different in a wide switching frequency range enabled by the GaN device, two peak current limits are used to control the buck-boost converter. When switching frequency is in the lower range, the peak current is set to the lower value (around 0.4 A) so a smaller inductor can be selected. When switching frequency is in the higher range, the peak current will be raised to the higher value (around 1 A) and will require a larger inductor. There is a filter on this frequency detection logic, therefore the LMG342xR030 requires 5 consecutive cycles at the higher frequency before it is set to the higher buck-boost peak current limit. Remember that the current limit will not go down again until power off once the higher limit is set. It will not change even when switching frequency goes back to the lower range.

For recommendations on the required passives, see [Section 10.2.2.3](#).

9.3.4 VDD Bias Supply

With a LDO to supply internal low voltage circuits and a buck-boost converter to regulate the gate voltage, the input is able to support wide VDD voltage range from 7.5 V to 18 V. However, the maximum switching frequency is de-rated for input voltages less than 9 V. TI recommends to have a 12-V unregulated power supply to supply VDD. No specific external LDO is needed.

9.3.5 Auxiliary LDO

There is a 5-V voltage regulator inside the part used to supply external loads, such as digital isolators for the high-side drive signal. The digital outputs of the part use this rail as their supply. No capacitor is required for stability, but transient response will be poor if no external capacitor is provided. If the application uses this rail to supply external circuits, TI recommends to have a capacitor of at least 0.1 μ F for improved transient response. A larger capacitor can be used for further transient response improvement. The decoupling capacitor used here should be a low-ESR ceramic type.

9.3.6 Fault Detection

The GaN power IC integrates overcurrent protection (OCP), short-circuit protection (SCP), overtemperature protection (OTP) and undervoltage lockout (UVLO).

9.3.6.1 Overcurrent Protection and Short-Circuit Protection

There are two types of current faults which can be detected by the driver: overcurrent fault and short-circuit fault.

The overcurrent protection (OCP) circuit monitors drain current and compares that current signal with an internally set limit. Upon detection of the overcurrent, the LMG342xR030 conducts cycle-by-cycle overcurrent protection as shown in [Figure 9-3](#). In this mode, the GaN device is shut off when overcurrent happens, but the overcurrent signal will clear after the input PWM goes low. In the next cycle, the GaN device can turn on as normal. The cycle-by-cycle function can be used in cases where steady-state operation current is below the OCP level but transient response can still reach current limit, while the circuit operation cannot be paused. It also prevents the GaN device from overheating by having overcurrent induced conduction loss.

The short-circuit protection (SCP) monitors drain current and compares that current signal with an internally set limit higher than that of OCP as shown in [Figure 9-4](#). It is designed to protect the GaN device from high-current short-circuit fault. When SCP happens at high current, the driver is intentionally slowed down to obtain lower di/dt . Therefore, lower overshoot voltage and ringing can be achieved during the turn-off event. On detection of the overcurrent, LMG342xR030 conduct latched turn-off. This fast response circuit could protect the GaN device even under a hard short-circuit condition. In this protection, the GaN device is shut off and held off until the fault is reset by either holding the IN pin low for a period of time defined in [Section 7](#) or removing power from VDD.

During OCP or SCP in a half bridge, after the current reaches the upper limit and the device is turned off by protection, the PWM input of the device could still be high and the PWM input of the complementary device could still be low. In this case, the load current can flow through the third quadrant of the complementary device with no synchronous rectification. The extra high negative voltage drop (-6 V to -8 V) from drain to source could lead to high third-quadrant loss, similar to dead time loss but with much longer time. [Section 9.3.9](#) offers adaptive dead time and reduces third-quadrant loss.

For safety considerations, OCP allows cycle-by-cycle operation while SCP will latch the device until reset. By reading the $\overline{\text{FAULT}}$ and $\overline{\text{OC}}$ pins, the exact current fault type can be determined. Refer to [Section 9.3.6.4](#) for detailed information.

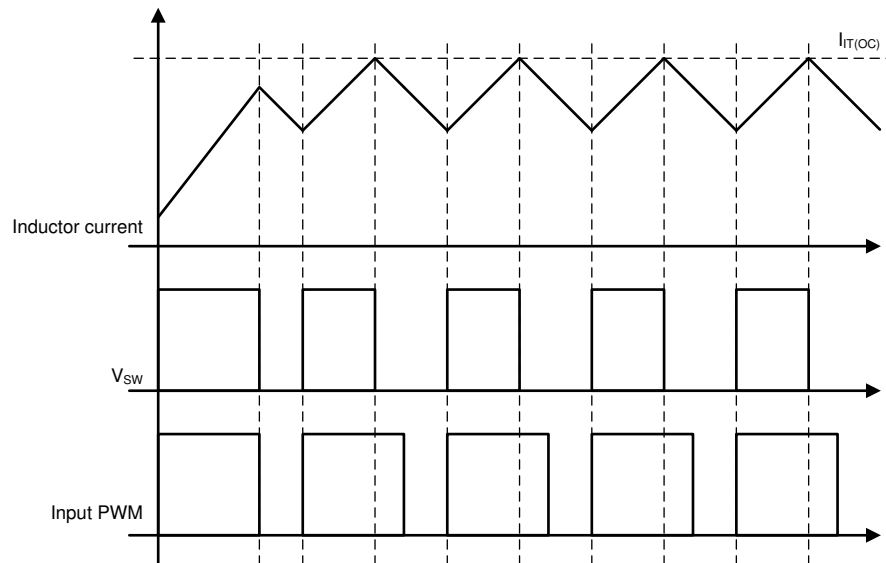


Figure 9-3. Cycle-by-Cycle OCP Operation

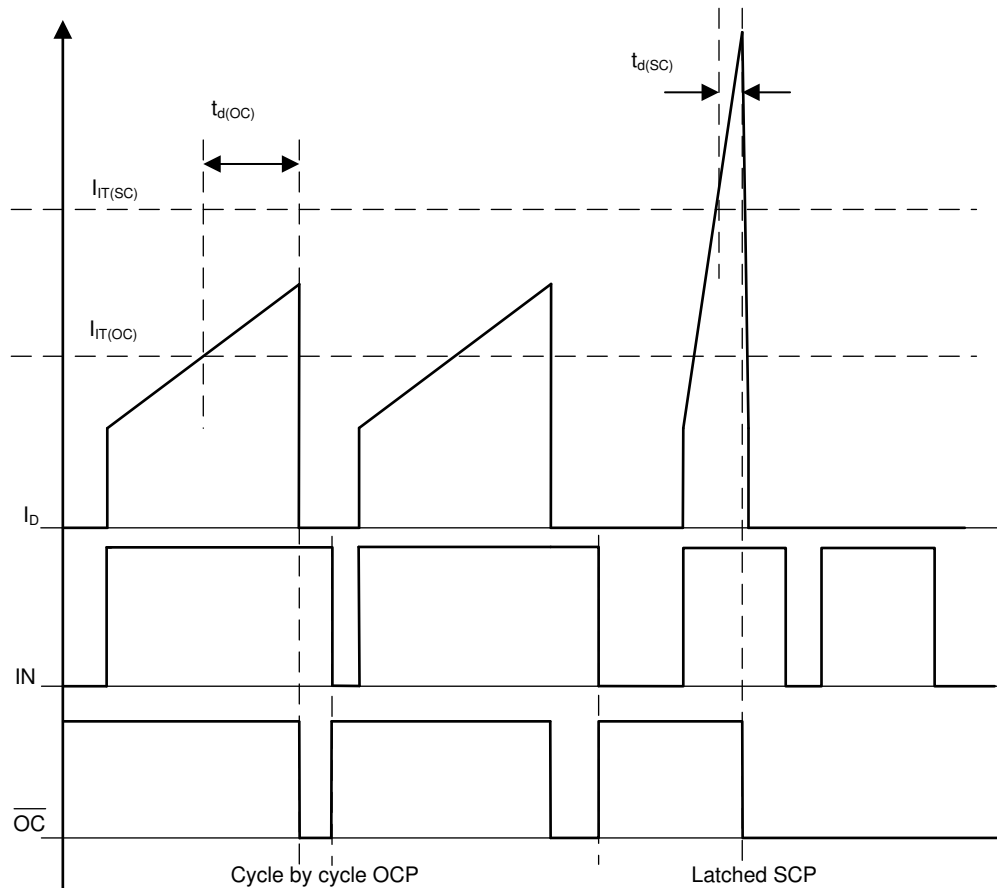


Figure 9-4. Overcurrent Detection vs. Short-Circuit Detection

9.3.6.2 Overtemperature Shutdown

There are two overtemperature shutdown thresholds in the part. The first one measures the GaN die temperature and trips around 165 °C. When it trips, the power IC disables switching and asserts the $\overline{\text{FAULT}}$ pin, but maintains the buck-boost and external LDO. During the overtemperature shutdown, the GaN device is held off until the temperature falls below the hysteresis limit, typically 20 °C below the turn-off threshold. This is not a latched protection scheme. In most applications, disabling the switching will allow the device to cool off. However, if there is instead a short circuit in the VNEG rail or the external 5-V LDO, the driver die temperature will continue to rise. If the silicon driver die temperature exceeds 185 °C, it will also shut down the buck-boost and the external LDO.

If the GaN die is over 165 °C and the overtemperature shutdown is active, but the driver is not over 185 °C where the buck-boost shuts down, the part will operate as an ideal diode that ignores the input and turns on and off automatically when it detects third-quadrant current. This is to lower the power dissipated in the GaN in third-quadrant operation.

9.3.6.3 UVLO Protection

The LMG342xR030 supports a wide range of VDD voltage. However, when the device is below UVLO threshold, the GaN device will stop switching and be held off. The $\overline{\text{FAULT}}$ pin will be pulled low as an indication of UVLO. The LDO is turned on by the rising-edge of the VIN UVLO and shut off around 5 V to 6 V.

9.3.6.4 Fault Reporting

The $\overline{\text{FAULT}}$ and $\overline{\text{OC}}$ outputs form a fault reporting scheme together. They are both push-pull outputs indicating the readiness and fault status of the driver. These two pins are logic high in normal operation, and will change logic according to Table 9-1.

Table 9-1. Fault Types and Reporting

	NORMAL	UVLO, OT, and RDRV-OPEN	OVERCURRENT	SHORT-CIRCUIT
FAULT	1	0	1	0
OC	1	1	0	0

FAULT is held low when starting up until the series Si FET is turned on. During operation, if the power supplies go below the UVLO thresholds or the device temperature go above the OT thresholds, power device is disabled and FAULT is held low until the power supplies or the device temperature recover. If RDRV is open, FAULT is also held low. In an short-circuit or overtemperature fault condition, FAULT is held low until the fault latches are reset or fault is cleared. The OC pin will be held low if there is a short-circuit or overcurrent fault. The signals help notify the controller the exact type of faults by reading the truth table. If a combined reporting of the faults on a single pin is desired, one can short the OC pin to ground during power up. All faults will assert the FAULT pin then and the OC pin will not be used. Internal protection happens regardless the connection of pin outputs, however.

9.3.7 Drive Strength Adjustment

The LMG342xR030 allows users to adjust the drive strength of the device and obtain desired slew rate, which provides the flexibility to optimize switching loss and noise coupling.

To adjust drive strength, a resistor can be placed between the RDRV pin and GND pin. The resistance determines the slew rate of the device, from 30 V/ns to 150 V/ns, during turn-on. On the other hand, there are two dv/dt values that can be selected without the resistor: shorting the RDRV pin to ground provides 150 V/ns of slew rate, and shorting the RDRV pin to 5 V provides 100 V/ns of slew rate.

9.3.8 Temperature-Sensing Output

The integrated driver senses the GaN die temperature and outputs the information through a modulated PWM signal on the TEMP pin. The typical PWM frequency is 11 kHz with the same refresh rate. The minimum PWM duty cycle is around 1%, which can be observed at temperature below 25 °C. The target temperature range is from 25 °C to 150 °C, and the corresponding PWM duty cycle is typically from 3% to 80%. At temperatures above 150 °C, the duty cycle will continue to increase linearly until overtemperature fault happens. When overtemperature happens, the TEMP pin will be pulled high to indicate this fault until the temperature is reduced to the normal range. There is a hysteresis to clear overtemperature fault.

9.3.9 Sync-FET Mode Operation

GaN devices do not have body diodes, but is still able to conduct current in third-quadrant (source to drain) when it is OFF. However, the voltage drop of GaN devices is higher than that of Si diodes during third-quadrant conduction. This results in higher power loss if not handled properly. The excessive loss can be observed in prolonged dead time or cycle-by-cycle current limit mode, leading to overtemperature, which could trigger protective shut down. To mitigate this problem, a Sync-FET Mode operation is implemented in the power IC.

Figure 9-5 shows how Sync-FET Mode operation achieves adaptive dead time and reduces third-quadrant loss in a boost converter. Before IN Pin of the free-wheeling IC goes high, the IC is able to detect the third-quadrant current and automatically turn ON GaN device after $t_{d(idm_on)}$, typically around 35ns. When IN Pin of the free-wheeling IC goes low, GaN device is turned OFF. After turn-off transient, there is a blanking time, t_{3rd_Blank} , typically around 115ns, to prevent the unwanted re-turn on during dead time.

A state machine has been also used to summarize the Sync-FET Mode operation. Please see Figure 9-6. In a half bridge:

- For the hard-switching IC in a half bridge
 - When IN Pin goes high, GaN device is always turned ON, and the hard-switching IC starts conducting first-quadrant current.
 - When IN Pin goes low, GaN device is turned OFF, and the hard-switching IC starts blocking positive V_{DS} .
 - When t_{3rd_Blank} expires, GaN device stays OFF, and the hard-switching IC starts detecting first-quadrant current, including both conduction and leakage current.

- When leakage current and positive V_{DS} presents, GaN device stays OFF and keeps blocking before IN Pin of the hard-switching IC goes high.
- For the free-wheeling IC in a half bridge
 - When IN Pin goes high, GaN device is always turned ON, and the free-wheeling IC starts conducting third-quadrant current at negative V_{DS} , product of negative I_D and $R_{DS(on)}$.
 - When IN Pin goes low, GaN device is turned OFF, and the free-wheeling IC starts conducting third-quadrant current at V_{SD} , third-quadrant mode source-drain voltage.
 - When t_{3rd_Blank} expires, GaN device stays OFF and continues third-quadrant conduction, and the free-wheeling IC starts detecting first-quadrant current, including both conduction and leakage current.
 - When first-quadrant current and positive V_{DS} presents at turn ON of the hard-switching IC, GaN device stays OFF but starts blocking, and the free-wheeling IC starts detecting third-quadrant current.
 - When third-quadrant current and negative V_{DS} presents at turn OFF of the hard switching IC, GaN device stays OFF during detection, t_{3rd_Det} , and then is turned ON by Sync-FET Mode. In Sync-FET Mode, the free-wheeling IC keeps detecting first-quadrant current, including both conduction and leakage current, before IN Pin goes high.
 - If first-quadrant current presents before IN Pin goes high, GaN device will be turned OFF, and the free-wheeling IC will NOT be turned ON again by Sync-FET Mode before IN Pin goes high.

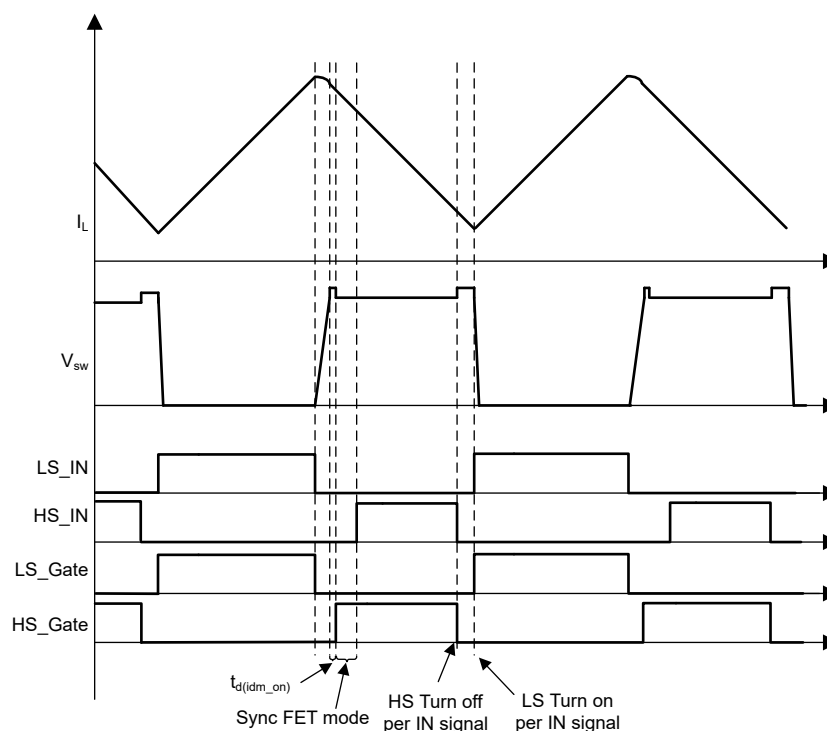


Figure 9-5. Dead Time Reduction In Sync Mode Operation

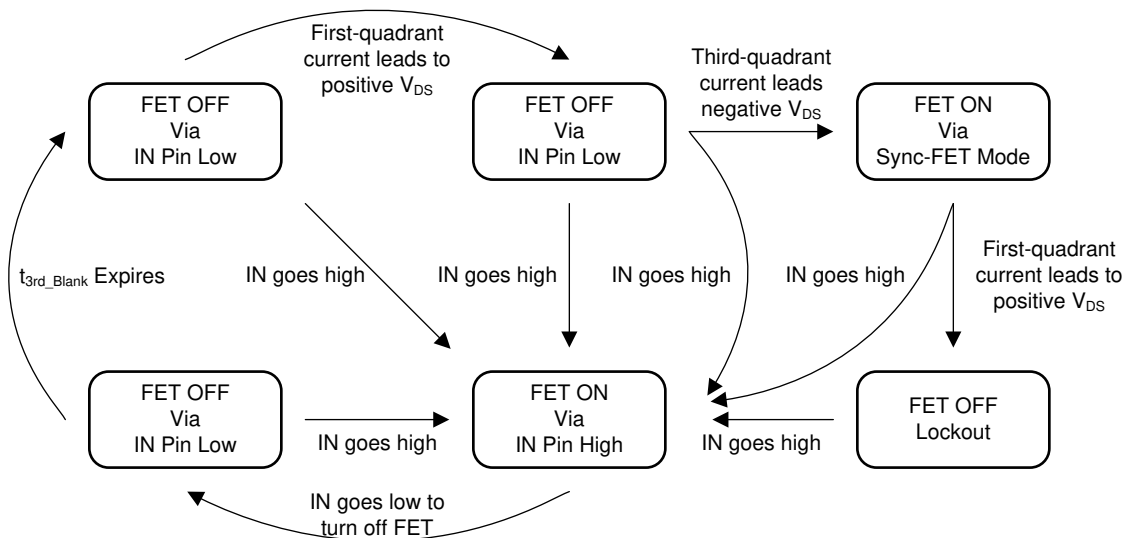


Figure 9-6. Sync FET Mode State Machine

9.4 Device Functional Modes

The device has one mode of operation that applies when operated within the Recommended Operating Conditions.

10 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

10.1 Application Information

The LMG342xR030 is a power IC targeting hard-switching and soft-switching applications running up to 480V bus voltage. GaN devices offer zero reverse-recovery charge enabling high-frequency, hard-switching applications like the totem-pole PFC. Low Q_{oss} of GaN devices also benefits soft-switching converters, such as the LLC and phase-shifted full-bridge configurations. As half-bridge configurations are the foundation of those applications, this section will describe how to use the LMG342xR030 in half-bridge configuration.

10.2 Typical Application

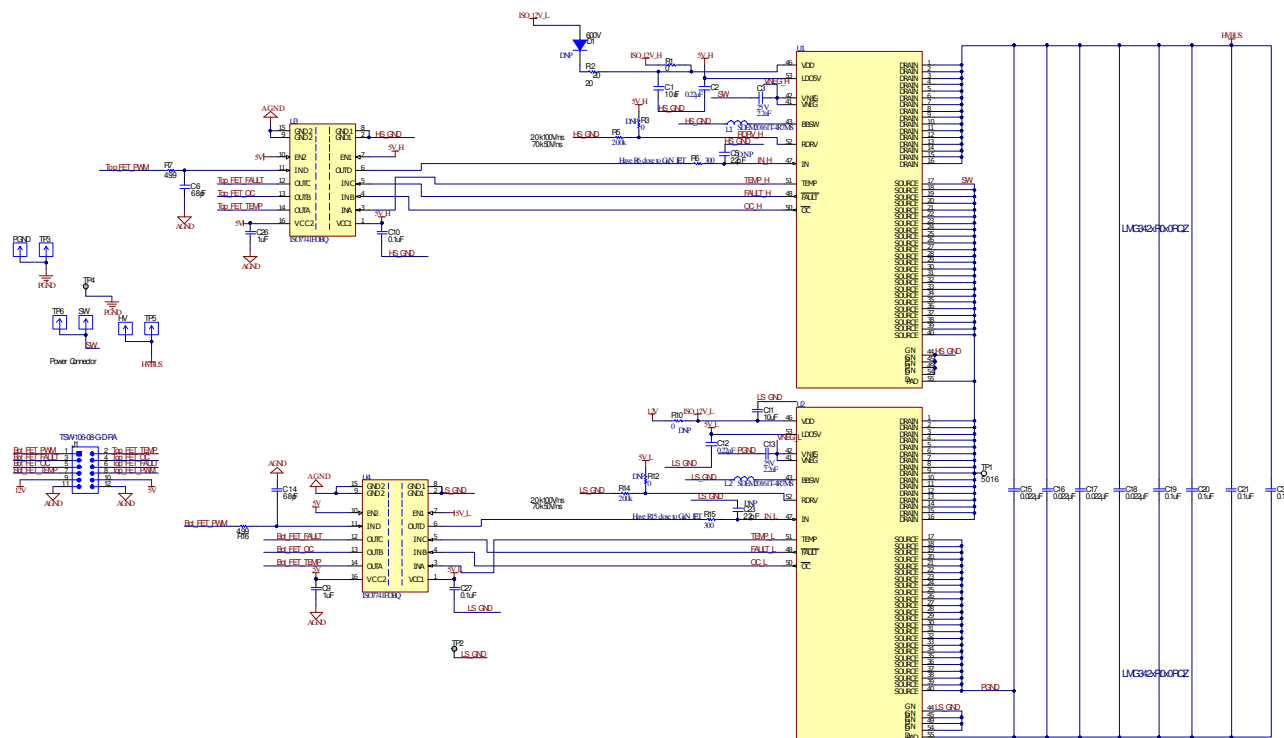


Figure 10-1. Typical Half-Bridge Application

10.2.1 Design Requirements

This design example is for a hard-switched boost converter which is representative of PFC applications. The system parameters for this design are shown in [Table 10-1](#).

Table 10-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage	200 VDC
Output voltage	400 VDC
Input (inductor) current	20 A
Switching frequency	100 kHz

10.2.2 Detailed Design Procedure

In high-voltage power converters, circuit design and PCB layout are essential for high-performance power converters. As designing a power converter is out of the scope of this document, this data sheet describes how to build well-behaved half-bridge configurations with the LMG342xR030.

10.2.2.1 Slew Rate Selection

The slew rate of LMG342xR030 can be adjusted between approximately 20 V/ns and 150 V/ns by connecting a resistor, R_{DRV} , from the RDRV pin to GND. The slew rate affects GaN device performance in terms of:

- Switching loss
- Voltage overshoot
- Noise coupling
- EMI emission

Generally, high slew rates provide low switching loss, but high slew rates can also create higher voltage overshoot, noise coupling, and EMI emission. Following the design recommendations in this data sheet will help mitigate the challenges caused by a high slew rate. The LMG342xR030 offers circuit designers the flexibility to select the proper slew rate for the best performance of their end equipment.

10.2.2.1.1 Start-Up and Slew Rate With Bootstrap High-Side Supply

Using a bootstrap supply introduces additional constraints on the start-up of the high-side LMG342xR030. Prior to powering up, the GaN device operates in cascode mode with reduced performance. In some circuits, a proper slew rate may be required for the start-up of a bootstrap-supplied half-bridge configuration.

10.2.2.2 Signal Level-Shifting

In half-bridges, high-voltage level shifters or digital isolators must be used to provide isolation for signal paths between the high-side device and control circuit. Using an isolator is optional for the low-side device. But, it will equalize propagation delays between the high-side and low-side signal path, and provide the ability to use different grounds for the GaN device and the controller. If an isolator is not used on the low-side device, the control ground and the power ground must be connected at the device and nowhere else on the board. See [Section 12.1](#) for more information. With the fast-switching GaN device, common ground inductance could easily cause noise issues without the use of an isolator.

Choosing a digital isolator for level-shifting is important for improvement of noise immunity. As GaN device can easily create high dv/dt , >50 V/ns, in hard-switching applications, it is highly recommended to use isolators with high common-mode transient immunity (CMTI). Isolators with low CMTI can easily generate false signal, which could cause shoot-through. On the other hand, it is strongly encouraged to select isolators which are not edge-triggered. In an edge-triggered isolator, a high dv/dt event can cause the isolator to flip states and cause circuit malfunctioning.

Generally, ON/OFF keyed isolators are preferred, such as the TI ISO77xxF series, as a high CMTI event would only cause a very short false pulse, a few nanoseconds, which can be filtered out. To filter these false pulses, a low pass filter, like 1 k Ω and 22 pF R-C filter, is recommended to be placed at the driver input.

10.2.2.3 Buck-Boost Converter Design

The buck-boost converter generates the negative voltage to turn off the direct-drive GaN device. While it is controlled internally, it requires an external power inductor and output capacitor. The converter is designed to use a 4.7- μ H inductor and a 2.2- μ F output capacitor.

As the peak current of the buck-boost is subject to two different peak current limits which are 0.4 A and 1 A for low and high frequencies (see [Section 9.3.3](#)), the inductor must have a saturation current well above the rated peak current limit. Once the higher limit is established at higher switching frequency, the current limit will not go down again even when GaN device is back to lower switching frequency. Therefore, it is critical to select the inductor according to maximum GaN switching frequency.

The buck-boost converter uses a peak current hysteretic control. As shown in [Figure 10-2](#), the inductor current increases at the beginning of a switching cycle until the inductor reaches the peak current limit. The inductor current will go down to zero. The idle time between each current pulse is determined automatically by the output current, and can be reduced to zero. Therefore, the maximum output current happens when the idle time is zero, and is decided by the peak current but irrelevant to the inductor value.

A minimum inductance value of 3 μ H is preferred for the buck-boost converter so that the di/dt across the inductor is not too high. This leaves enough margin for the control loop to respond. As a result, the maximum di/dt of the inductor is limited to 6 A/ μ s. On the other hand, large inductance also limits the transient response for stable output voltage, and it is preferred to have inductors less than 10 μ H.

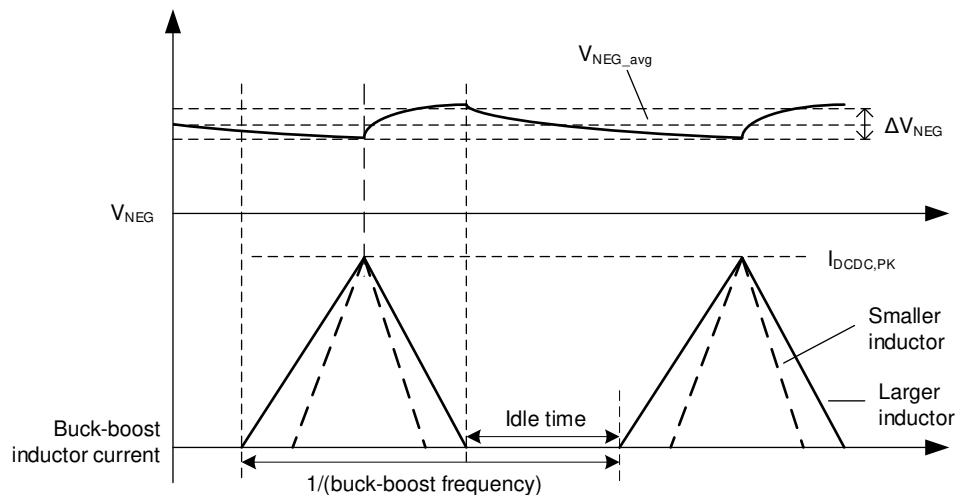


Figure 10-2. Buck-Boost Converter Inductor Current

10.3 Do's and Don'ts

The successful use of GaN devices in general and the LMG342xR030 in particular depends on proper use of the device. When using the LMG342xR030, **DO**:

- Read and fully understand the datasheet, including the application notes and layout recommendations.
- Use a four-layer board and place the return power path on an inner layer to minimize power-loop inductance.
- Use small, surface-mount bypass and bus capacitors to minimize parasitic inductance.
- Use the proper size decoupling capacitors and locate them close to the IC as described in [Section 12.1](#).
- Use a signal isolator to supply the input signal for the low-side device. If not, ensure the signal source is connected to the signal GND plane which is tied to the power source **only** at the LMG342xR030 IC.
- Use the FAULT pin to determine power-up state and to detect overcurrent and overtemperature events and safely shut off the converter.

To avoid issues in your system when using the LMG342xR030, **DON'T**:

- Use a single-layer or two-layer PCB for the LMG342xR030 as the power-loop and bypass capacitor inductances will be excessive and prevent proper operation of the IC.
- Reduce the bypass capacitor values below the recommended values.
- Allow the device to experience drain transients above 600 V as they may damage the device.
- Allow significant third-quadrant conduction when the device is OFF or unpowered, which may cause overheating. Self-protection feature cannot protect the device in this mode of operation.
- Ignore the FAULT pin output.

11 Power Supply Recommendations

The LMG342xR030 only requires an unregulated 12-V supply. The low-side supply can be obtained from the local controller supply. The supply of the high-side device must come from an isolated supply or a bootstrap supply.

11.1 Using an Isolated Power Supply

Using an isolated power supply to power the high-side device has the advantage that it will work regardless of continued power-stage switching or duty cycle. It can also power the high-side device before power-stage switching begins, eliminating the power-loss concern of switching with an unpowered LMG342xR030 (see [Section 10.2.2.1.1](#) for details). Finally, a properly-selected isolated supply will introduce less parasitics and reduce noise coupling.

The isolated supply can be obtained with a push-pull converter, a flyback converter, a FlyBuck™ converter, or an isolated power module. When using an unregulated supply, the input of LMG342xR030 should not exceed the maximum supply voltage. A 16-V TVS diode could be used to clamp the VDD voltage of LMG342xR030. Minimizing the inter-winding capacitance of the isolated power supply or transformer is necessary to reduce switching loss in hard-switched applications.

11.2 Using a Bootstrap Diode

In half-bridge configuration, a floating supply is necessary for the high-side device. To obtain the best performance of LMG342xR030, [Section 11.1](#) is highly recommended. A bootstrap supply can be used with the recommendations of this section.

11.2.1 Diode Selection

The LMG342xR030 offers no reverse-recovery charge and very limited output charge. Hard-switching circuits using the LMG342xR030 also exhibit high voltage slew rates. A compatible bootstrap diode should not introduce high output charge and reverse-recovery charge.

A silicon carbide diode, like the GB01SLT06-214, can be used to avoid reverse-recovery effects. The SiC diode has an output charge of 3 nC. Although there is additional loss from its output charge, it does not dominate the losses of the switching stage.

11.2.2 Managing the Bootstrap Voltage

In a synchronous buck or other converter where the low-side switch occasionally operates in third-quadrant, the bootstrap supply charges through a path that includes the third-quadrant voltage drop of the low-side LMG342xR030 during the dead time as shown in [Figure 11-1](#). This third-quadrant drop can be large, which may over-charge the bootstrap supply in certain conditions. The V_{DD} supply of LMG342xR030 must be kept below 18 V.

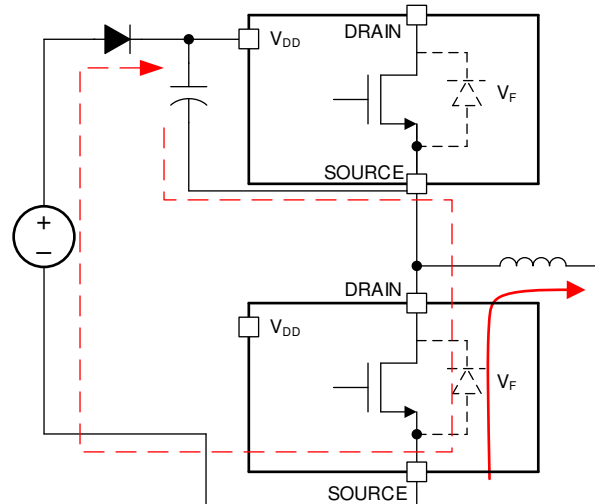


Figure 11-1. Charging Path for Bootstrap Diode

As shown in [Figure 11-2](#), the recommended bootstrap supply includes a bootstrap diode, a series resistor, and a 16-V TVS or zener diode in parallel with the V_{DD} bypass capacitor to prevent damaging the high-side LMG342xR030. The series resistor limits the charging current at start-up, and when the low-side device is operating in third-quadrant mode. This resistor must be selected to allow sufficient current to power the LMG342xR030 at the desired operating frequency. At 100-kHz operation, a value of approximately $2\ \Omega$ is recommended. At higher frequencies, this resistor value should be reduced or the resistor omitted entirely to ensure sufficient supply current.

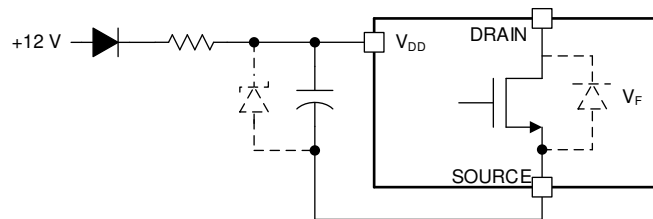


Figure 11-2. Suggested Bootstrap Regulation Circuit

12 Layout

12.1 Layout Guidelines

The layout of the LMG342xR030 is critical to its performance and functionality. Because the half-bridge configuration is typically used with these GaN devices, layout recommendations will be considered with this configuration. A four-layer or higher layer count board is required to reduce the parasitic inductances of the layout to achieve suitable performance.

12.1.1 Power Loop Inductance

The power loop, comprising the two devices in the half bridge and the high-voltage bus capacitance, undergoes high di/dt during switching events. By minimizing the inductance of this loop, ringing and electro-magnetic interference (EMI) can be reduced, as well as reducing voltage stress on the devices.

Place the power devices as close as possible to minimize the power loop inductance. The decoupling capacitors are positioned in line with the two devices. They can be placed close to either device. In [Section 12.2](#), the decoupling capacitors are placed on the same layer as the devices. The return path (PGND in this case) is located on second layer in close proximity to the top layer. By using inner layer and not bottom layer, the vertical dimension of the loop is reduced, thus minimizing inductance. A large number of vias near both the device terminal and bus capacitance carries the high-frequency switching current to inner layer while minimizing impedance.

12.1.2 Signal Ground Connection

The LMG342xR030's SOURCE pin is internally connected to GND pins of the power IC, the signal ground reference. Local signal ground planes should be connected to GND pins with low impedance star connection. In addition, the return path for the passives associated to the driver (for example, bypass capacitance) must be connected to the GND pins. In [Section 12.2](#), local signal ground planes are located on second layer to act as the return path for the local circuitry. The local signal ground planes are not connected to the high-current SOURCE pins except the star connection at GND pins.

12.1.3 Bypass Capacitors

The gate drive loop impedance must be minimized to obtain good performance. Although the gate driver is integrated on package, the bypass capacitance for the driver is placed externally. As the GaN device is turned off to a negative voltage, the impedance of the path to the external VNEG capacitor is included in the gate drive loop. The VNEG capacitor must be placed close to VNEG and GND pins.

The bypass capacitors for the input supply, C1 and C11, and the 5-V regulator, C2 and C12, must also be placed close to the power IC with low impedance connections.

12.1.4 Switch-Node Capacitance

GaN devices have very low output capacitance and switch quickly with a high dv/dt , yielding very low switching loss. To preserve this low switching loss, additional capacitance added to the output node must be minimized. The PCB capacitance at the switch node can be minimized by following these guidelines:

- Minimize overlap between the switch-node plane and other power and ground planes.
- Thin the GND return path under the high-side device somewhat while still maintaining a low-inductance path.
- Choose high-side isolator ICs and bootstrap diodes with low capacitance.
- Place the power inductor as close to the GaN device as possible.
- Power inductors should be constructed with a single-layer winding to minimize intra-winding capacitance.
- If a single-layer inductor is not possible, consider placing a small inductor between the primary inductor and the GaN device to effectively shield the GaN device from the additional capacitance.
- If a back-side heat-sink is used, restrict the switch-node copper coverage on the bottom copper layer to the minimum area necessary to extract the needed heat.

12.1.5 Signal Integrity

The control signals to the LMG342xR030 must be protected from the high dv/dt caused by fast switching. Coupling between the control signals and the drain may cause circuit instability and potential destruction. Route

the control signals (IN, $\overline{\text{FAULT}}$ and $\overline{\text{OC}}$) over a ground plane placed on an adjacent layer. In [Section 12.2](#), for example, all the signals are routed on layers close to the local signal ground plane.

Capacitive coupling between the traces for the high-side device and the static planes, such as PGND and HVBUS, could cause common mode current and ground bounce. The coupling can be mitigated by reducing overlap between the high-side traces and the static planes. For the high-side level shifter, ensure no copper from either the input or output side extends beneath the isolator or the CMTI of the device may be compromised.

12.1.6 High-Voltage Spacing

Circuits using the LMG342xR030 involve high voltage, potentially up to 600V. When laying out circuits using the LMG342xR030, understand the creepage and clearance requirements for the application and how they apply to the GaN device. Functional (or working) isolation is required between the source and drain of each transistor, and between the high-voltage power supply and ground. Functional isolation or perhaps stronger isolation (such as reinforced isolation) may be required between the input circuitry to the LMG342xR030 and the power controller. Choose signal isolators and PCB spacing (creepage and clearance) distances which meet your isolation requirements.

If a heat sink is used to manage thermal dissipation of the LMG342xR030, ensure necessary electrical isolation and mechanical spacing is maintained between the heat sink and the PCB.

12.1.7 Thermal Recommendations

The LMG342xR030 is a lateral device grown on a Si substrate. The thermal pad is connected to the source of device. The LMG342xR030 may be used in applications with significant power dissipation, for example, hard-switched power converters. In these converters, cooling using just the PCB may not be sufficient to keep the part at a reasonable temperature. To improve the thermal dissipation of the part, TI recommends a heatsink is connected to the back of the PCB to extract additional heat. Using power planes and numerous thermal vias, the heat dissipated in the LMG342xR030(s) can be spread out in the PCB and effectively passed to the other side of the PCB. A heat sink can be applied to bare areas on the back of the PCB using an thermal interface material (TIM). The soldermask from the back of the board underneath the heat sink can be removed for more effective heat removal.

Refer to the [High Voltage Half Bridge Design Guide for LMG3410 Smart GaN FET](#) application note for more recommendations and performance data on thermal layouts.

12.2 Layout Examples

Correct layout of the LMG342xR030 and its surrounding components is essential for correct operation. The layouts shown here reflect the GaN device schematic in [Figure 10-1](#). These layouts are shown to produce good results and is intended as a guideline. However, it may be possible to obtain acceptable performance with alternate layout schemes. On the other hand, please refer to land pattern example in [Section 14](#) for the latest recommended PCB footprint of device.

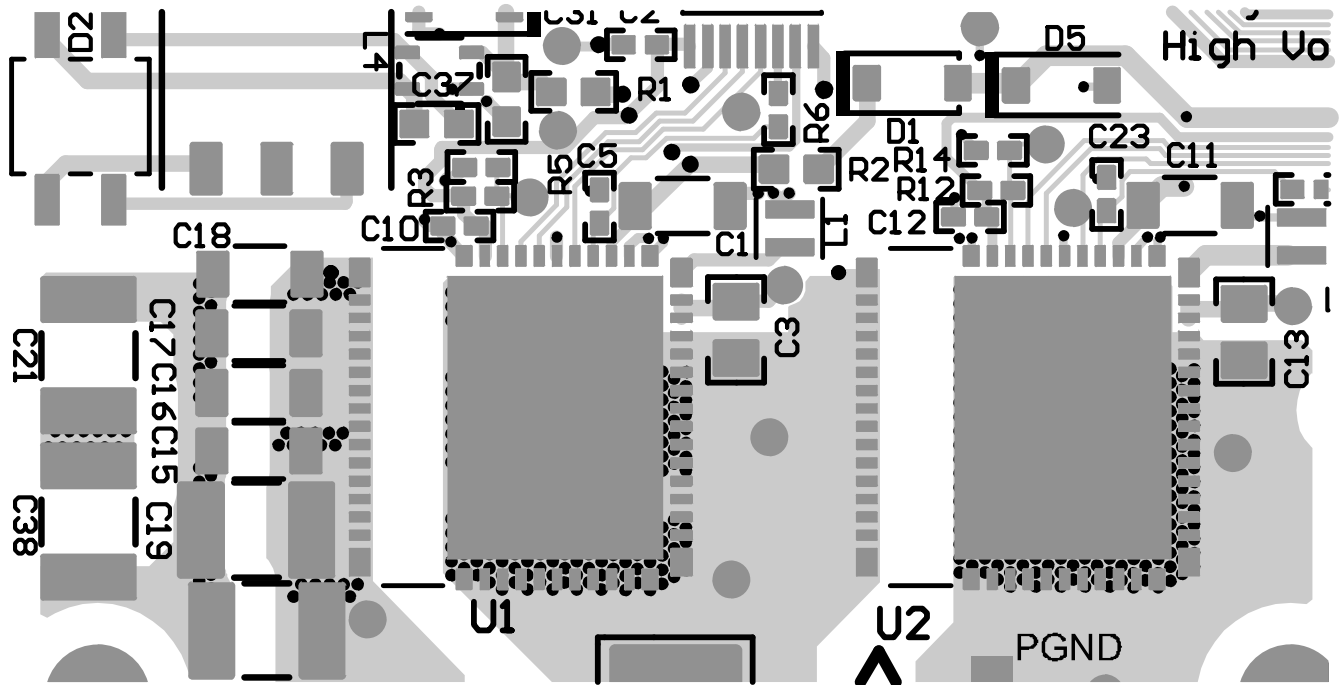


Figure 12-1. Half-Bridge Top Layer Layout

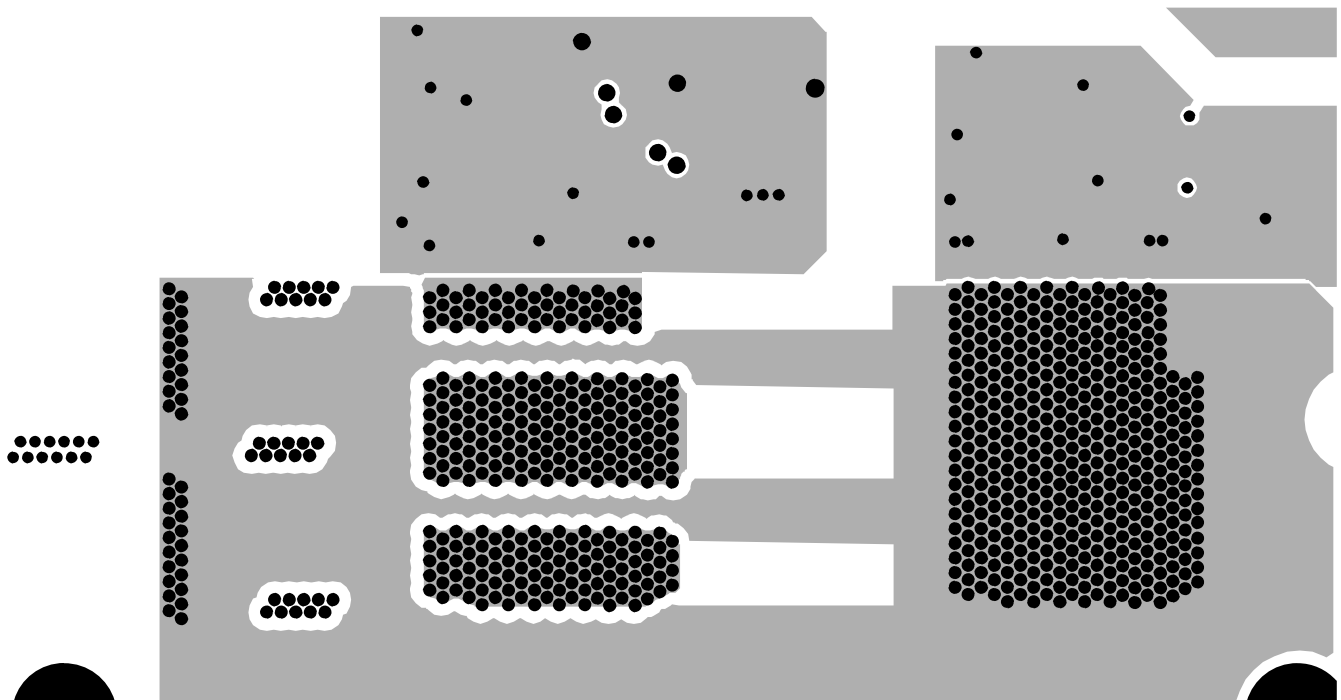


Figure 12-2. Half-Bridge Mid Layer Layout

13 Device and Documentation Support

13.1 Documentation Support

13.1.1 Related Documentation

[High Voltage Half Bridge Design Guide for LMG3410 Smart GaN FET](#) application note.

13.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

13.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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13.4 Trademarks

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13.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.6 Export Control Notice

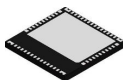
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13.7 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

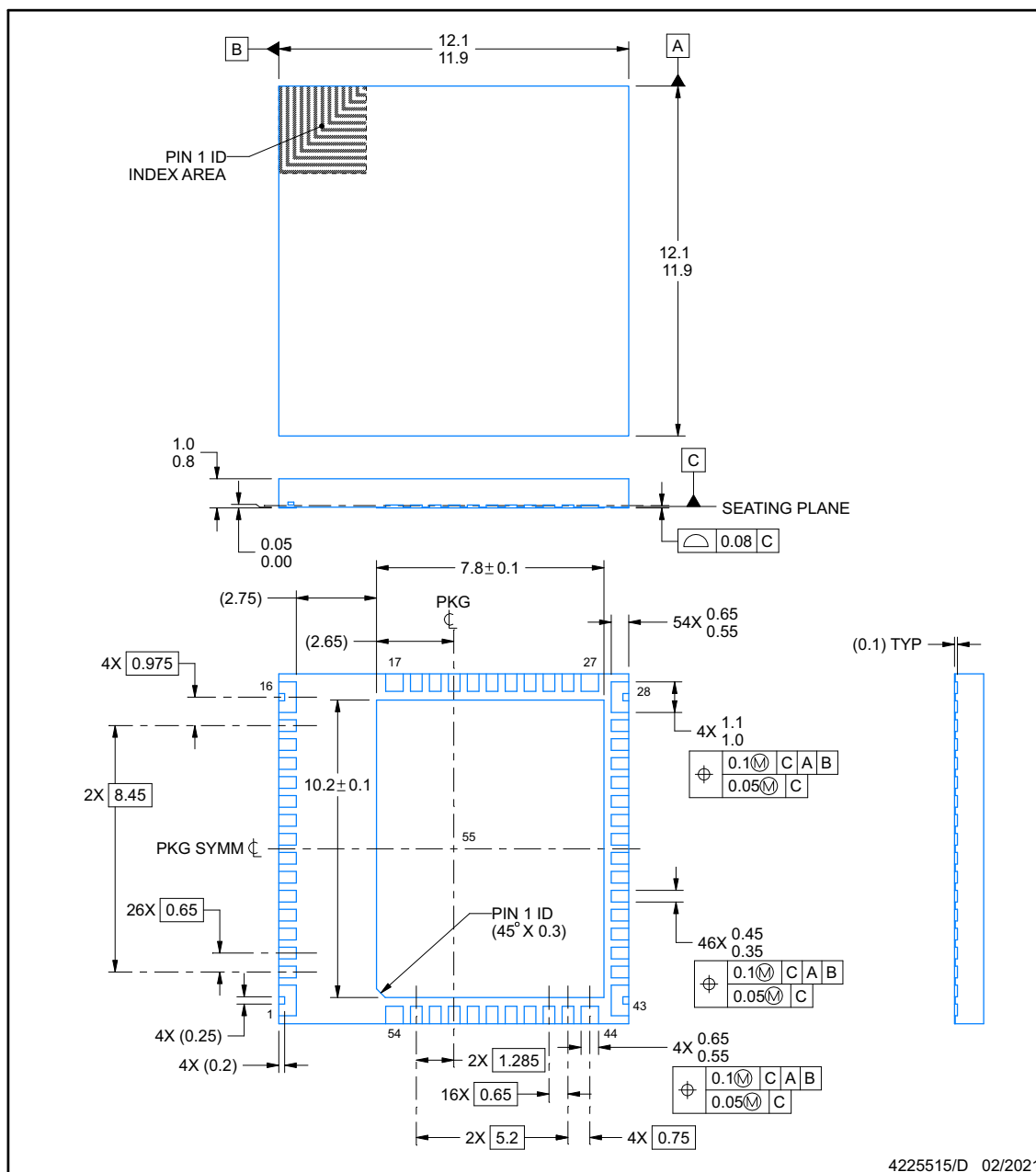
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



RQZ0054A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



ADVANCE INFORMATION

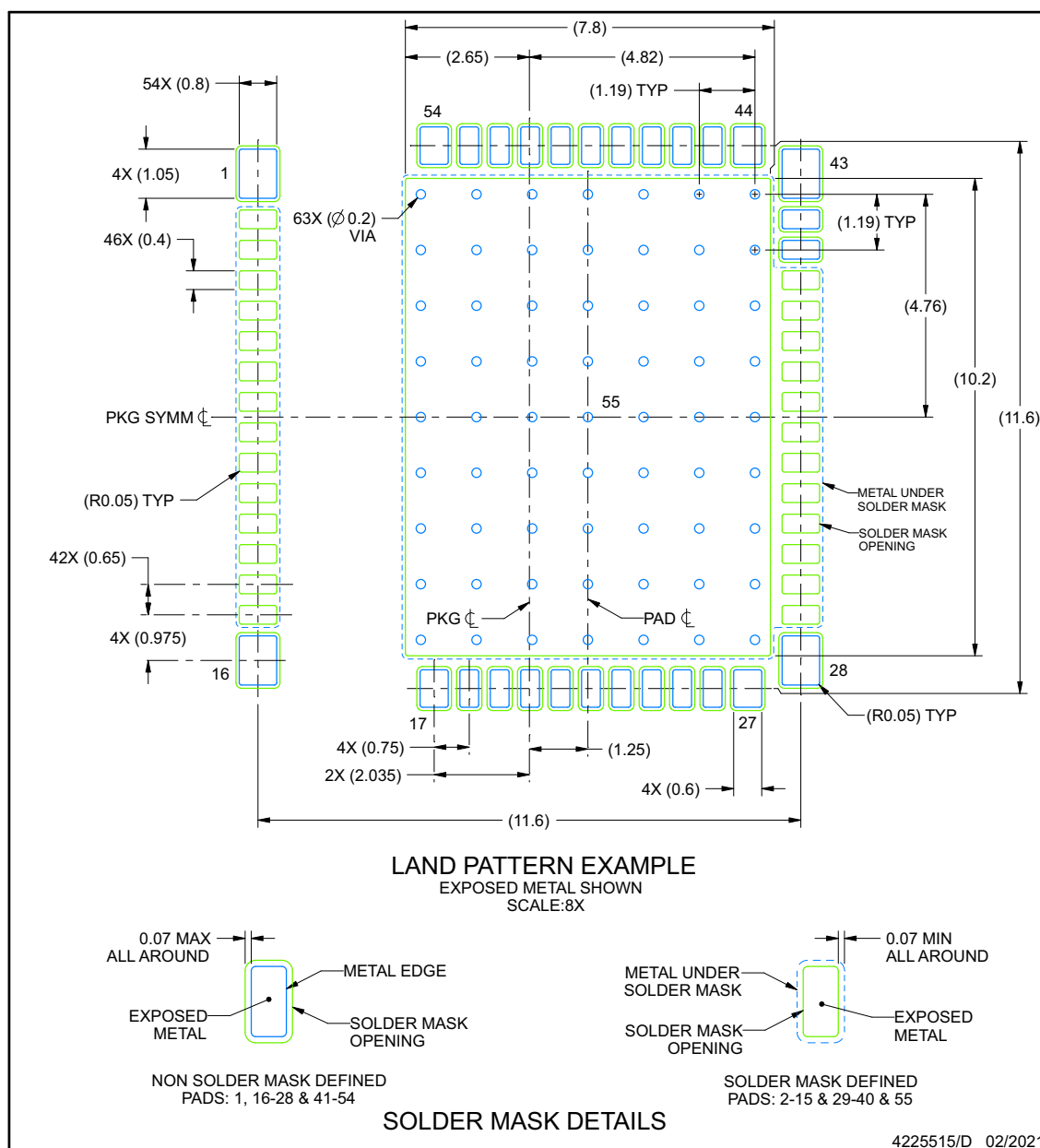
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

RQZ0054A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

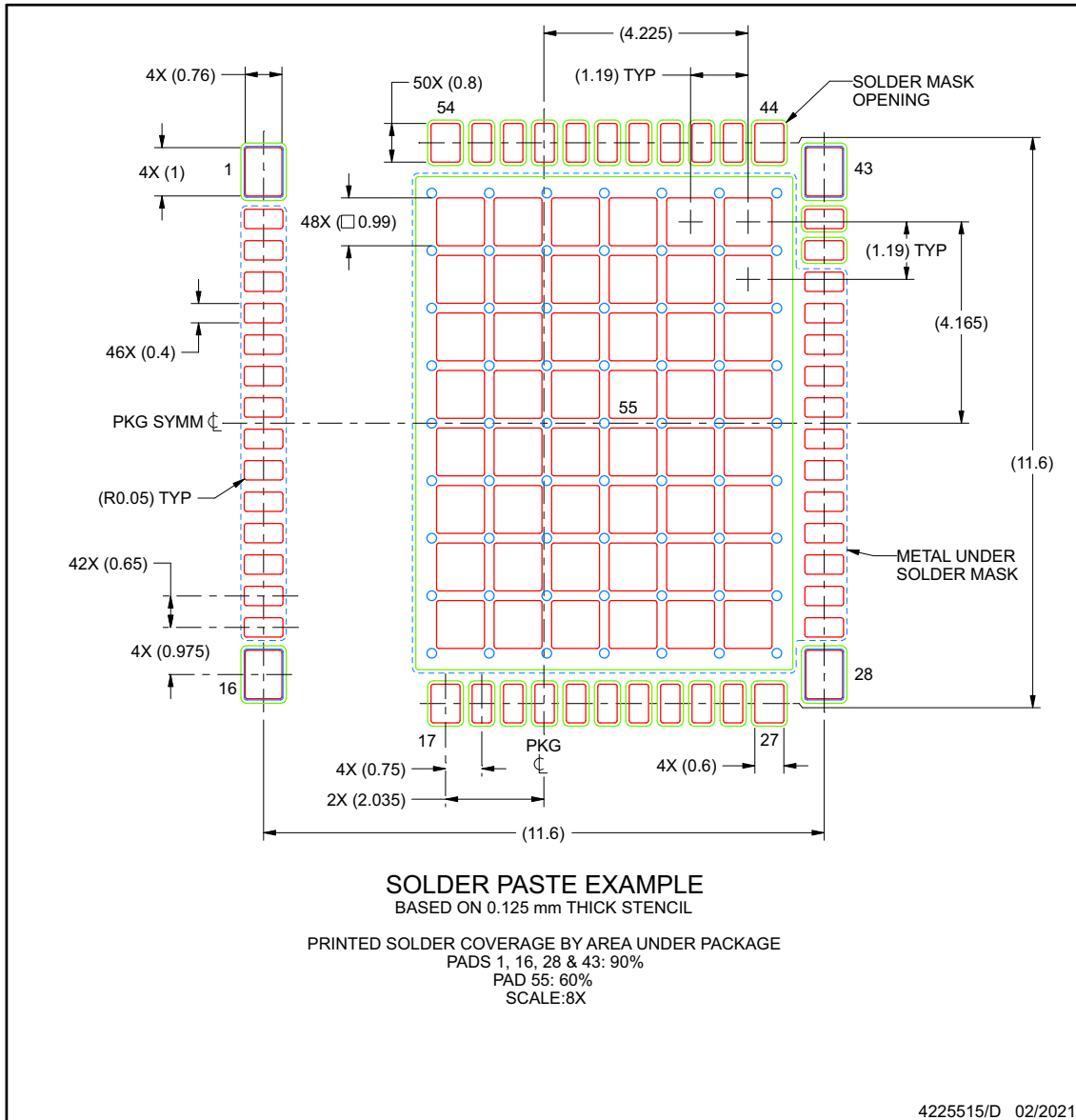
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

EXAMPLE STENCIL DESIGN

RQZ0054A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
XLMG3422R030RQZT	ACTIVE	VQFN	RQZ	54	250	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		Samples
XLMG3425R030RQZT	ACTIVE	VQFN	RQZ	54	250	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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